

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-35 (Canceled)

36. (Original) A semiconductor processing component comprising silicon carbide, the component having a surface having an R_a less than about 2 microns, and an impurity content of less than about 1000 ppm along an outer portion of the component as measured by SIMS at a depth of 10 nm from the surface of the component.

37. (Currently Amended) The ~~method-component~~ of claim 36, wherein the component comprises a substrate and a silicon carbide coating thereon.

38. (Currently Amended) The ~~method-component~~ of claim 36, wherein the component is machined to have said R_a less than about 2 microns.

39. (Currently Amended) The ~~method-component~~ of claim 36, wherein said impurity content is less than about 500 ppm.

40. (Currently Amended) The ~~method-component~~ of claim 36, wherein said impurity content is less than about 200 ppm.

41. (Original) A semiconductor processing component for receiving a semiconductor wafer, the component having a surface having an R_a less than about 2 microns, and an impurity content of less than about 1000 ppm along an outer portion of the component, as measured by SIMS at depth of 10 nm from the surface.